

Applications

- IEEE802.11b DSSS WLAN
- IEEE802.11g,n OFDM WLAN
- Access Points

Features

- Dual Mode IEEE802.11b, IEEE802.11g, IEEE802.11n
- 26 dBm, EVM = 3%, 802.11g, OFDM 54 Mbps
- 29 dBm, ACPR < -32 dBc, 802.11b
- Integrated PA, Input Match, 2.8V reference voltage generator
- Integrated Temperature Compensated, Positive Slope Power Detector
- Pb-free, RoHS compliant and Halogen-free
- 3 mm x 3 mm x 0.9 mm, MSL 3

Product Description

The SE2576L is a high power 802.11bgn WLAN power amplifier module providing the functionality of the power amplifier, power detector, reference voltage generator and input match.

The SE2576L is designed for ease of use and maximum flexibility, with an integrated input match, and external output match to adjust the load line for 5V, 26dBm operation.

The SE2576L includes a temperature compensated transmit power detector with over 20 dB of dynamic range and <1.2dB variation under 3:1 mismatch at the antenna.

The SE2576L includes a digital enable control due to an integrated reference voltage generator. The power ramp rise/fall time is 0.5 μ s typical.

Ordering Information

Part No.	Package	Remark
SE2576L	16 pin QFN	Samples
SE2576L-R	16 pin QFN	Tape & Reel
SE2576L-EK1	N/A	Evaluation kit

Functional Block Diagram

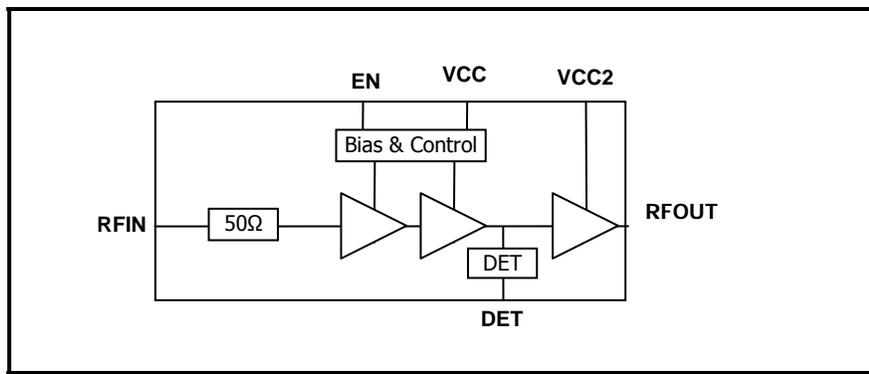


Figure 1: Functional Block Diagram

Pin Out Diagram

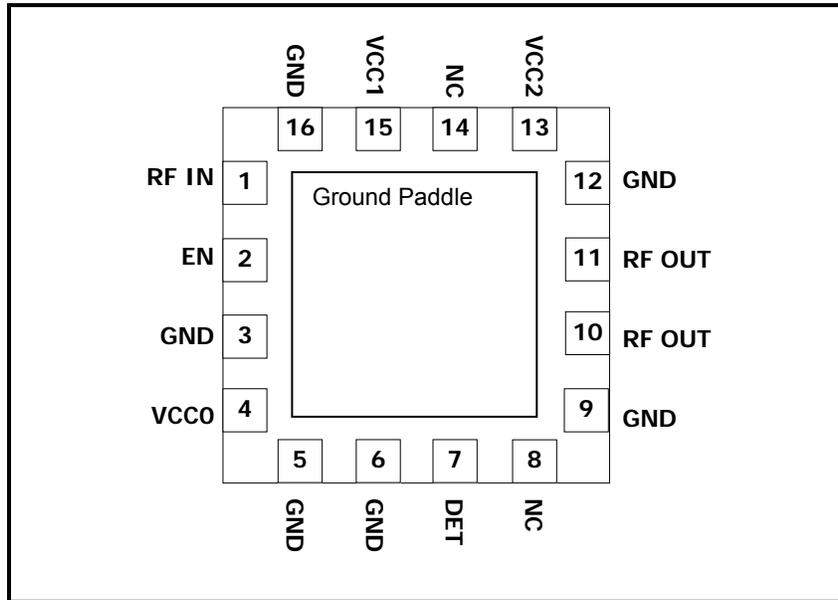


Figure 2: SE2576L Pin Out (Top View Through Package)

Pin Out Description

Pin No.	Name	Description
1	RF IN	RF Input
2	EN	Power Amplifier Enable
3	GND	Ground
4	VCC0	Power Supply for Bias Circuit
5	GND	Ground
6	GND	Ground
7	DET	Power Detector Output
8	NC	No Connect. May be left floating or grounded.
9	GND	Ground
10	RF OUT	RF Output
11	RF OUT	RF Output
12	GND	Ground
13	VCC2	Power Supply for 2 nd Stage
14	NC	No Connect. May be left floating or grounded.
15	VCC1	Power Supply driver stages
16	GND	Ground
Die paddle	GND	Ground

Absolute Maximum Ratings

These are stress ratings only. Exposure to stresses beyond these maximum ratings may cause permanent damage to, or affect the reliability of the device. Avoid operating the device outside the recommended operating conditions defined below. This device is ESD sensitive. Handling and assembly of this device should be at ESD protected workstations.

Symbol	Definition	Min.	Max.	Unit
VCC0, 1, 2	Supply Voltage on VCC	-0.3	5.5	V
V _{IN}	DC input on EN	-0.3	3.6	V
TX	RF Input Power. RF Out terminated in 50Ω	-	12.0	dBm
T _A	Operating Temperature Range	-40	85	°C
T _{STG}	Storage Temperature Range	-40	150	°C

Recommended Operating Conditions

Symbol	Parameter	Min.	Typ.	Max.	Unit
T _A	Ambient temperature	-40	25	85	°C
VCC	Supply voltage, relative to GND = 0 V	4.5	5	5.5	V

DC Electrical Characteristics

Conditions: VCC = 5 V, EN = V_{ENH}, T_A = 25 °C, as measured on SiGe Semiconductor's SE2576L-EV1 evaluation board (de-embedded to device), all unused ports terminated with 50 ohms, unless otherwise noted

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _{CC-G}	Total Supply Current	P _{OUT} = 26 dBm, 54 Mbps OFDM signal, 64QAM	-	500	-	mA
I _{CC-B}	Total Supply Current	P _{OUT} = 29 dBm, 11 Mbps CCK signal, BT = 0.45	-	650	-	mA
I _{CC-OFF}	Total Supply Current	EN = 0 V, No RF Applied	-	10	100	μA

Logic Characteristics

Conditions: VCC = 5 V, EN = V_{ENH}, T_A = 25 °C, as measured on SiGe Semiconductor's SE2576L-EV1 evaluation board (de-embedded to device), all unused ports terminated with 50 ohms, unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V _{ENH}	Logic High Voltage (Module On)	-	1.8	-	3.6	V
V _{ENL}	Logic Low Voltage (Module Off)	-	0	-	0.4	V
I _{ENH}	Input Current Logic High Voltage	-	-	300	-	μA
I _{ENL}	Input Current Logic Low Voltage	V _{EN} = 0.4V	-	1	50	μA
Z _{EN}	Enable pin input impedance	Passive Pull Down		10		kΩ

AC Electrical Characteristics

802.11g/n Transmit Characteristics

Conditions: $V_{CC} = 5\text{ V}$, $V_{EN} = 3.3\text{ V}$, $T_A = 25\text{ }^\circ\text{C}$, as measured on SiGe Semiconductor's SE2576L-EV1 evaluation board (de-embedded to device), all unused ports terminated with 50 ohms, unless otherwise noted.

Symbol	Parameter	Condition	Min.	Typ.	Max.	Unit
F_{IN}	Frequency Range	-	2400	-	2500	MHz
P_{OUT}	Output Power	54 Mbps OFDM signal, 64 QAM, 3% EVM	-	26	-	dBm
ACPR, IEEE Mask	Spectral Mask	$P_{OUT} = 29\text{ dBm}$, 11 Mbps CCK, BT = 0.45 11 – 22 MHz 22 – 33 MHz	-	-35 -55	-	dBc
P_{1dB}	P1dB	-	-	32	-	dBm
S_{21}	Small Signal Gain	-	30	33	-	dB
ΔS_{21}	Small Signal Gain Variation	Gain variation over single 40MHz channel Gain Variation over band	- -	0.5 1.0	- -	dB
2f	Harmonics	$P_{OUT} = 29\text{ dBm}$, 1 Mbps, 802.11b	-	-50	-45	dBm/MHz
3f			-	-50	-45	dBm/MHz
t_{dr}, t_{df}	Delay and rise/fall Time	50 % of V_{EN} edge and 90/10 % of final output power level	-	0.5	-	μs
S_{11}	Input Return Loss	-	10	15	-	dB
STAB	Stability	CW, $P_{OUT} = 29\text{ dBm}$ 0.1 GHz – 20 GHz Load VSWR = 4:1	All non-harmonically related outputs less than -42 dBm/MHz			
RU	Ruggedness	CW 50% duty cycle, PIN = +12dBm, Load VSWR = 6:1	No permanent damage.			

Power Detector Characteristics

Conditions: VCC = 5 V, EN = VENH, TA = 25 °C, as measured on SiGe Semiconductor's SE2576L-EV1 evaluation board, unless otherwise noted.

Symbol	Parameter	Condition	Min.	Typ.	Max.	Unit
F _{OUT}	Frequency Range	-	2400	-	2500	MHz
PDR	Power detect range, CW	Measured at RF out	5	-	30	dBm
PDZ _{src}	DC source impedance on PD_OUT	-	-	2.3	-	KΩ
PDZ _{LOAD}	DC load impedance	-	-	26.5	-	KΩ
PDV _{P5}	Output Voltage, P _{OUT} = 5dBm CW	Measured into 26.5KΩ	-	0.33	-	V
PDV _{P26}	Output Voltage, P _{OUT} = 26 dBm CW	Measured into 26.5KΩ	-	0.70	-	V
PDV _{P30}	Output Voltage, P _{OUT} = 30 dBm CW	Measured into 26.5KΩ	-	1.00	-	V
LPF _{-3dB}	Power detect low pass filter -3dB corner frequency	Measured into 26.5KΩ	-	2.0	-	MHz

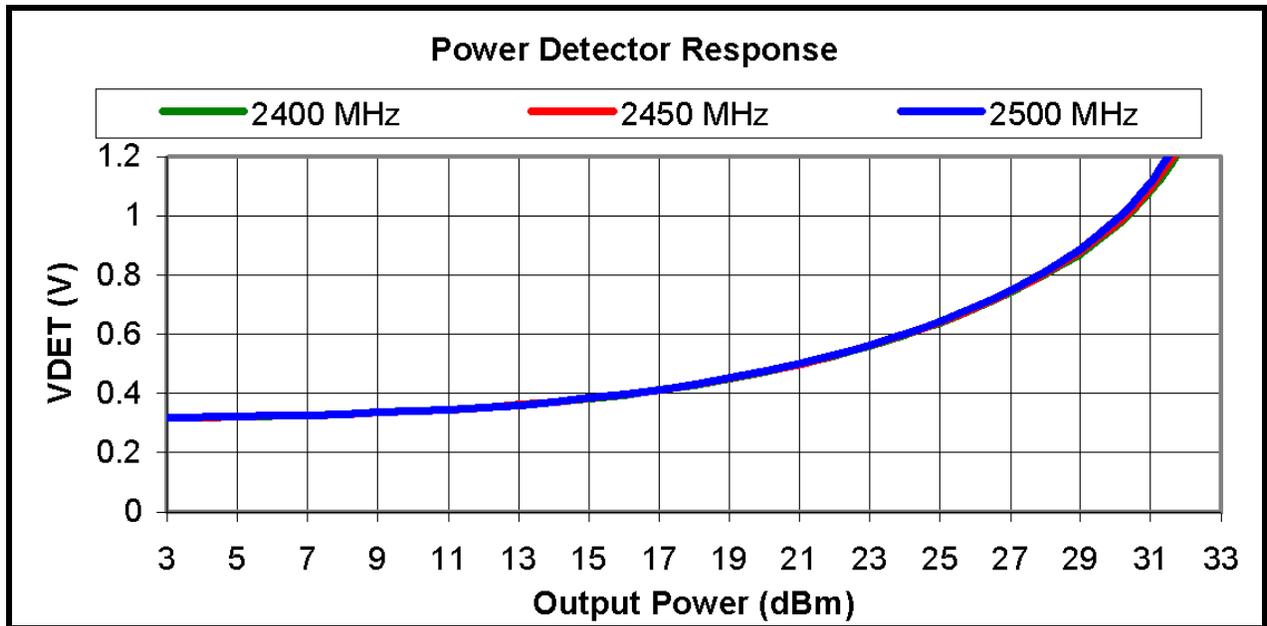


Figure 3: SE2576L Detector Characteristics

Package Diagram

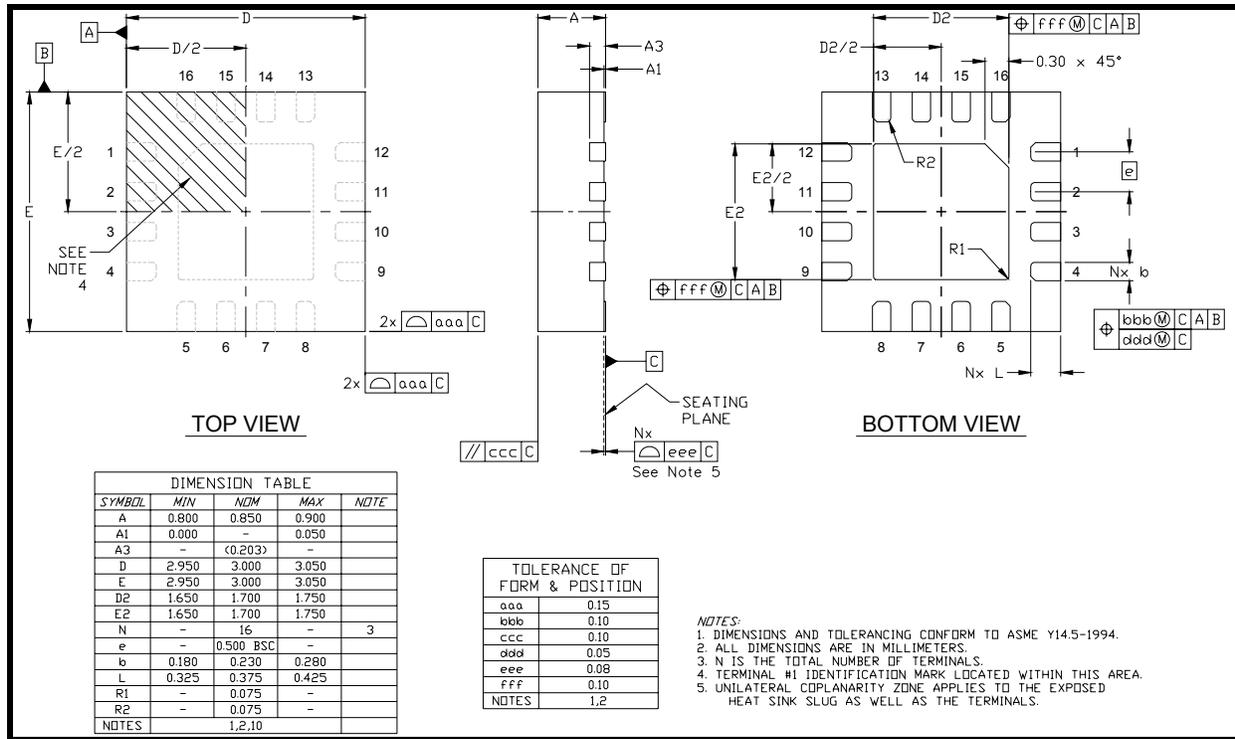


Figure 4: SE2576L Package Diagram

Recommended Land and Solder Patterns

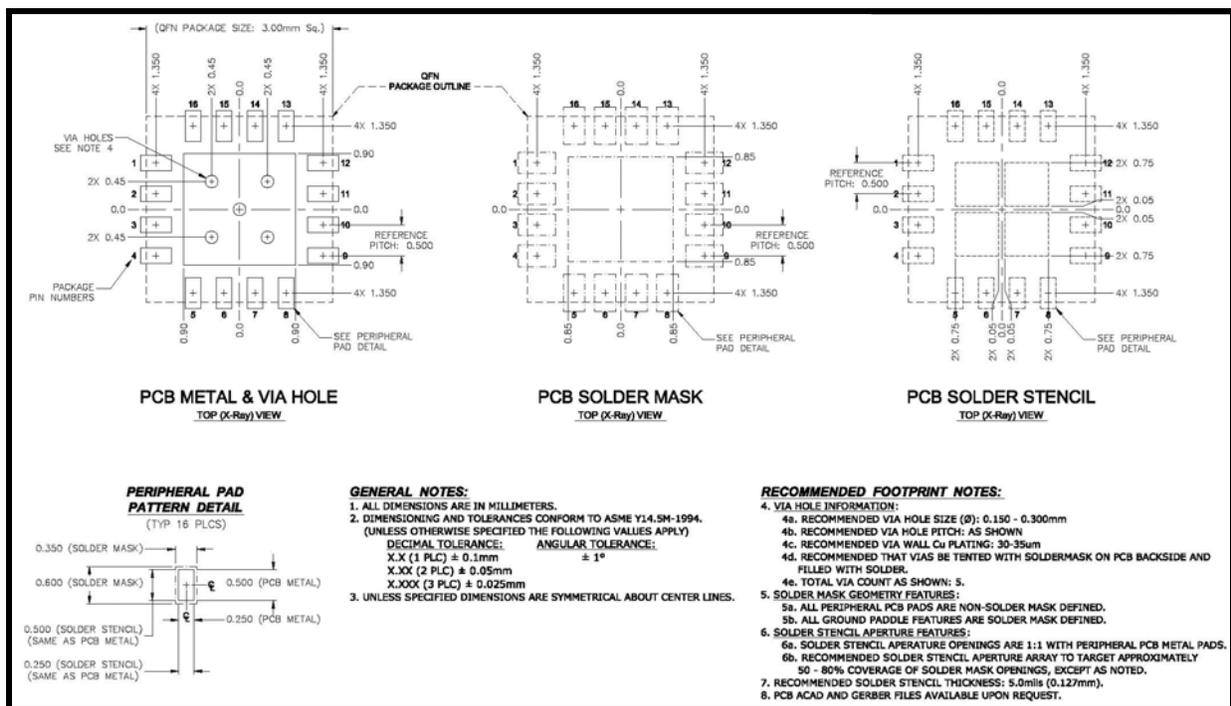


Figure 5: SE2576L Recommended Land and Solder Pattern

Package Handling Information

Because of its sensitivity to moisture absorption, instructions on the shipping container label must be followed regarding exposure to moisture after the container seal is broken, otherwise, problems related to moisture absorption may occur when the part is subjected to high temperature during solder assembly. The SE2576L is capable of withstanding a Pb free solder reflow. Care must be taken when attaching this product, whether it is done manually or in a production solder reflow environment. If the part is manually attached, precaution should be taken to insure that the device is not subjected to temperatures above its rated peak temperature for an extended period of time. For details on both attachment techniques, precautions, and handling procedures recommended by SiGe, please refer to:

- SiGe's Application Note: "Quad Flat No-Lead Module Solder Reflow & Rework Information", *Document Number QAD-00045*
- SiGe's Application Note: "Handling, Packing, Shipping and Use of Moisture Sensitive QFN", *Document Number QAD-00044*



Caution! Class 0 ESD sensitive device

Branding Information

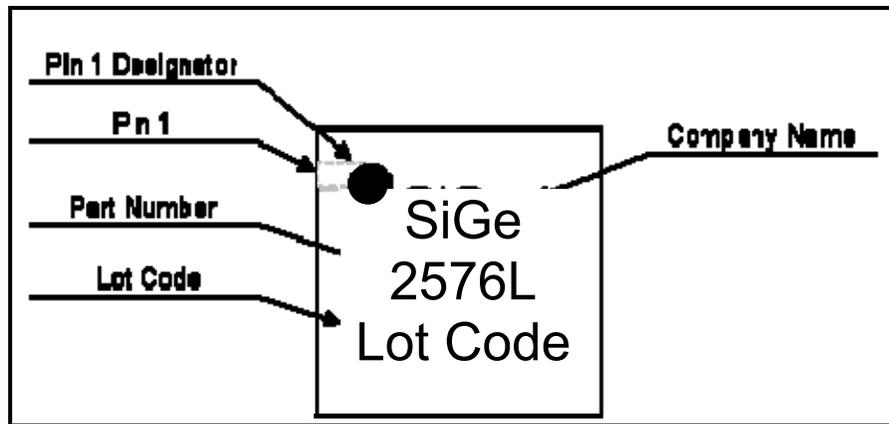


Figure 6: SE2576L Branding

Tape and Reel Information

Parameter	Value
Devices Per Reel	3000
Reel Diameter	13 inches
Tape Width	12 millimeters

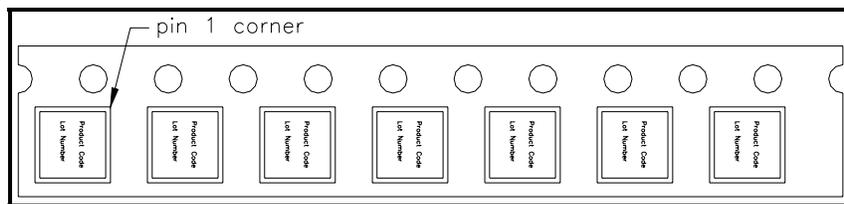


Figure 7: SE2576L-R Tape and Reel Information

Document Change History

Revision	Date	Notes
1.0	Jan 10, 2009	Created
1.1	May 8, 2009	Updated PA Control Logic Characteristics Updated POD for SE2576L datasheet.
1.2	Jul 8, 2009	Updated to correct pins 8 & 14 definitions.
1.3	Aug 2, 2009	Updated detector characteristics
1.4	Sep 24, 2009	Updated current consumption
1.5	Oct 25, 2009	Updated detector plot
1.6	Jan 25, 2010	Updated Off-State Leakage current
1.7	Jun 22, 2010	Extended operating temperature to Industrial limits

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Product Preview

The datasheet contains information from the product concept specification. SiGe Semiconductor, Inc. reserves the right to change information at any time without notification.

Preliminary Information

The datasheet contains information from the design target specification. SiGe Semiconductor, Inc. reserves the right to change information at any time without notification.

Production testing may not include testing of all parameters.

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